

## **AMENDMENTS TO THE CLAIMS**

The following listing of claims will replace all prior versions and listings of claims in the application.

### **LISTING OF CLAIMS**

1. (currently amended) A semiconductor device comprising:  
a fuse including an upper layer wiring layer having a first length;  
a first protection film on the fuse; and  
a second protection film on the first protection film, the second protection film including an opening section formed therein that exposes the first protection film;  
the opening section exposing an entire portion of the first protection film located directly above the fuse, and the first length being greater than a diameter of a laser that is used to irradiate the first protection film.
  
2. (original) A semiconductor device according to claim 1, wherein each of two end sections of the fuse is connected to a lower layer wiring layer through a via hole.

3. (currently amended) A method for manufacturing a semiconductor device, comprising:

a step of forming a fuse including of an upper layer wiring layer that has a first length on an upper surface of an interlayer dielectric layer that is formed on a substrate;

a step of forming a first protection film on an upper surface of the interlayer dielectric layer and the fuse;

a step of forming a second protection film on an upper surface of the first protection film; and

a step of forming an opening section in the second protection film, the opening section exposing an entire portion of the first protection film located directly above the fuse;

irradiating a portion of the first protection film with a laser having a diameter that is less than the first length.

4. (original) A method for manufacturing a semiconductor device according to claim 3, further comprising the steps of forming via holes in the interlayer dielectric layer, and connecting two ends of the fuse to a lower layer wiring layer through the via holes.

5. (cancelled)

6. (cancelled)

7. (cancelled)